IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
JUSTIN K. BRASK MARK L. DOCZY JACK KAVALIEROS UDAY SHAH MATTHEW V. METZ ROBERT S. CHAU ROBERT B. TURKOT, JR. Serial No.: unknown))))))) Art Unit: unknown
Sena No.: unknown) Examiner: unknown
Filed: unknown) Attorney Docket: P17821
For: A METHOD FOR ETCHING A THIN METAL LAYER)))
Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450	•

INFORMATION DISCLOSURE STATEMENT

Sir:

This Information Disclosure Statement is being submitted under 37 C.F.R. §1.97(b). Enclosed is a copy of Information Disclosure Citation Form PTO-1449 together with copies of the references cited on that form. It is respectfully requested that the cited references be considered and that the enclosed copy of Information Disclosure Citation Form PTO-1449 be initialed by the Examiner to indicate such consideration and a copy thereof returned to applicant(s).

Pursuant to 37 C.F.R. § 1.97, the submission of this Information Disclosure Statement is not to be construed as a representation that a search has been made

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Examiner		Date Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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